

# LHCb Vertex Detector Upgrade Plans

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# General Physics Justification for LHCb



- Expect New Physics will be seen at LHC
  - Standard Model is violated by the Baryon Asymmetry of Universe & by Dark Matter
  - Hierarchy problem (why  $M_{\text{Higgs}} \ll M_{\text{Planck}}$ )
- However, it will be difficult to characterize this physics
- How the new particles interfere virtually in the decays of b's (& c's) with W's & Z's can tell us a great deal about their nature, especially their phases

## LHCb Upgrade Goals

- Upgrade LHCb detector such that it can operate at 10 times design luminosity of  $\mathcal{L} \sim 2 \times 10^{33} \text{ cm}^{-2}\text{s}^{-1}$
- Accumulate  $\sim 100 \text{ fb}^{-1}$  without detector replacement
- Maximize sensitivity to many interesting hadronic channels  $\Rightarrow$  fast, efficient, and selective vertex trigger
- Present design luminosity is about a factor of 25 reduced from maximum luminosity that could be delivered to it  $\Rightarrow$  This upgrade does not need sLHC but is compatible with it

## Why upgrade?

- Determination of new physics effects requires high statistics ( $\sim 100 \text{ fb}^{-1}$ )
- For example:
  - Weak mixing phase  $\Phi_s$  studied through the time dependent asymmetry of flavor tagged  $B_s \rightarrow J/\Psi \Phi$  can be determined to an error of 0.003
  - CKM angle  $\gamma$  can be determined with an error of  $1^\circ$ - $2^\circ$  depending upon the channel used
  - Precision studies of rare decays such as  $B \rightarrow K^* \mu \mu$
  - Precision studies of CP violation in charm decays

# Trigger considerations

- Current L0 trigger:

- Reconstructs highest  $E_t$  hadron, electron,  $\gamma$  & two highest  $p_t \mu$

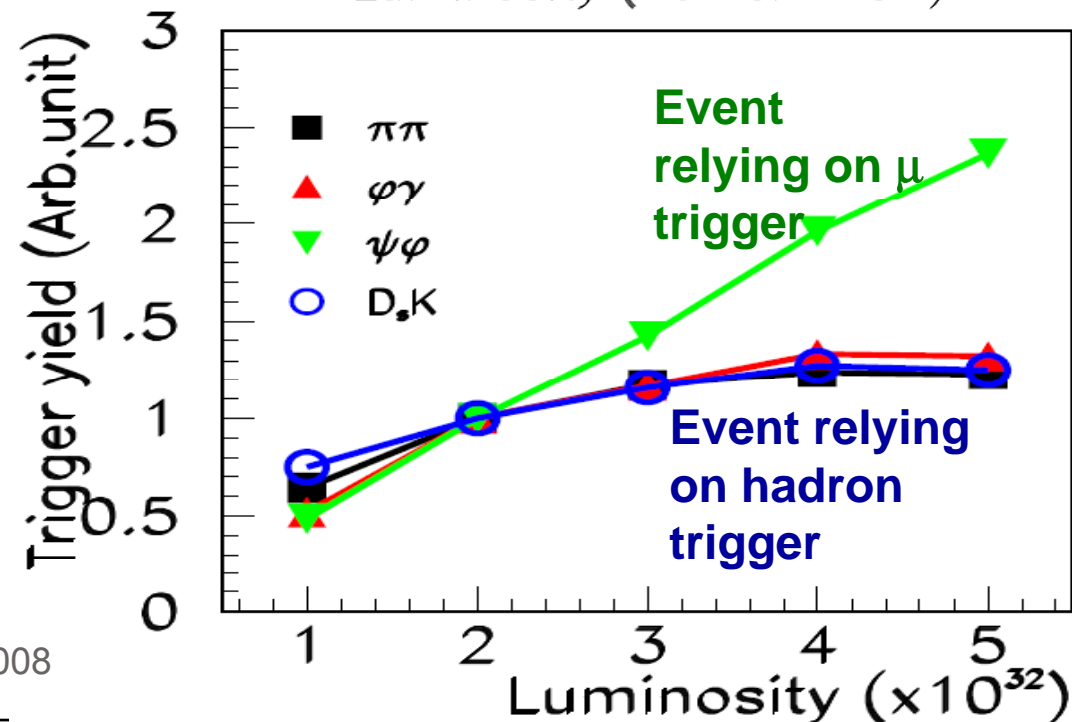
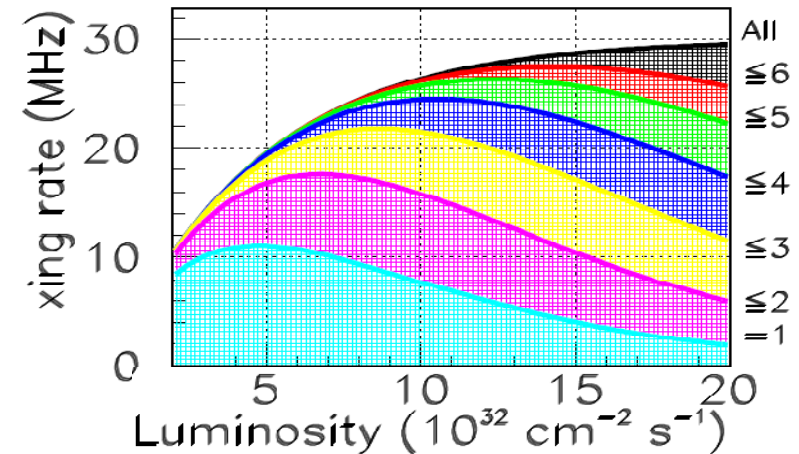
- Thresholds

1.  $E_T^{hadron} \geq 3.5$  GeV
2.  $E_T^{e,\gamma} \geq 2.5$  GeV
3.  $p_T^\mu \geq 1$  GeV

- Even at nominal luminosity #of interactions cut on (1) to stay below the 1MHz L0 rate

More details in  
LHCC/2008-007

rate of pp interactions



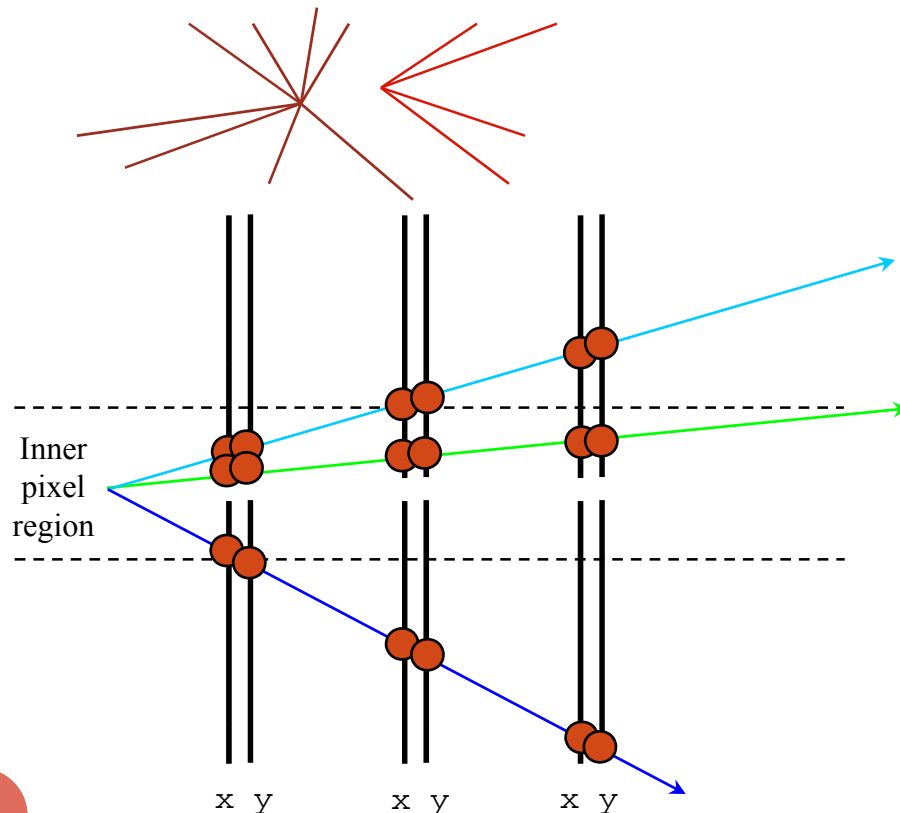
# To improve trigger performance on hadronic channels



- Measurement of both momentum and impact parameter of the B decay products
  - Data read out at 40 MHz  $\Leftrightarrow$  difficult to find algorithm that is sufficiently selective for hadronic B decays in “real time”
  - Identify best solution for fast and efficient measurement of momentum and impact parameter of the B hadron
    - ? Modification of present higher level hadronic B selection algorithm
    - ? Vertex detector in B field

# Possible Vertex Triggering

- ◆ Idea: find primary vertices & detached tracks from b or c decays



- ▶ Pixel hits from 3 stations are sent to a tracker that matches “interior” and “exterior track hits
- ▶ Interior and exterior triplets are sent to a CPU farm to complete the pattern recognition:
  - interior/exterior triplet matcher
  - fake-track removal
- See E. Gottschalk, *Nucl.Phys.Proc.Suppl.* 156, 252 (2006).



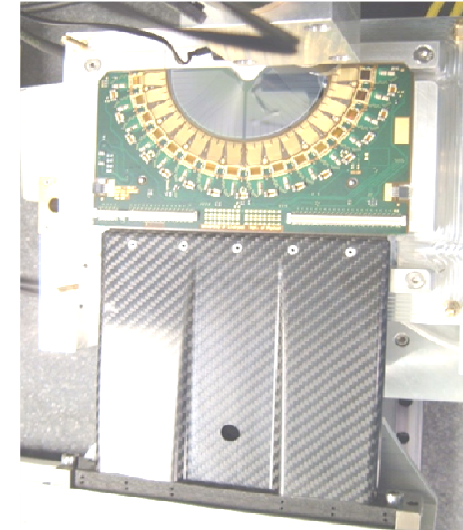
# Vertex detector requirements

- **Radiation resistance** ( $\sim 10^{16}$  1 MeV  $n_{eq}$  /cm<sup>2</sup>)
- 40 MHz readout: time stamp and information transferred to buffers synchronized with BCO
- Fast and robust pattern recognition capabilities  
⇒ detached vertex criteria almost “in real time”
- Optimization of impact parameter resolution
  - Reduce detector inner radius
  - RF foil modifications
- **Material minimization for chosen solution**

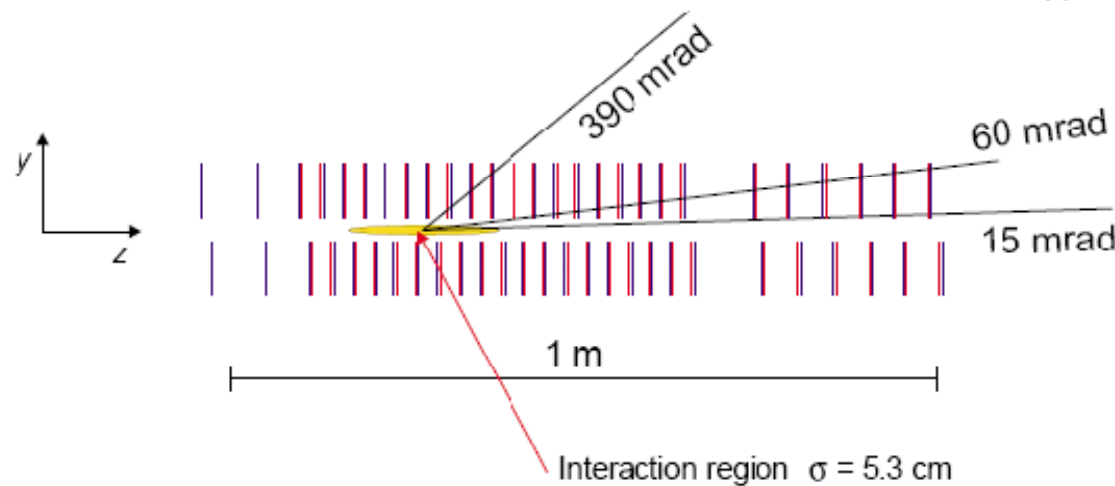


# Velo now

- $r\phi$  strip detector with variable pitch:
  - tradeoff between number of channels and resolution
  - Quick rz tracking for triggering purposes
- Radiation dose up to  $1.3 \times 10^{14}$  1 MeV  $n_{eq}/\text{year}$  ( $2\text{fb}^{-1}$ )



VELO Module



*Length determined by goal of matching full LHCb  $\eta$  coverage*

## Velo after ~3 years of operation

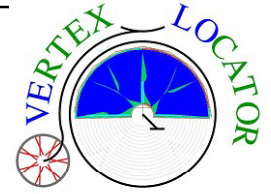


- ▶ Looks the same!
- ▶ Replacement of modules with sensors built on p-type substrates: first full scale sLHC type silicon detectors!
- ▶ EVELO concept of upgraded detector based on this system:
  - ▶ Reoptimization with smaller strip length, smaller inner pitch, rad-hard bias...

From VELO



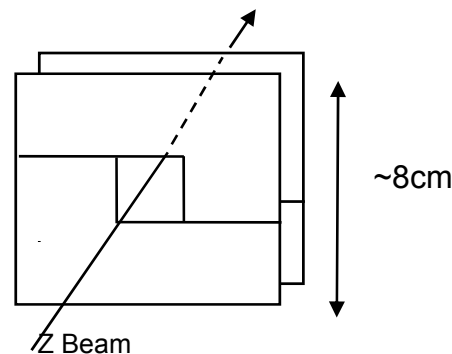
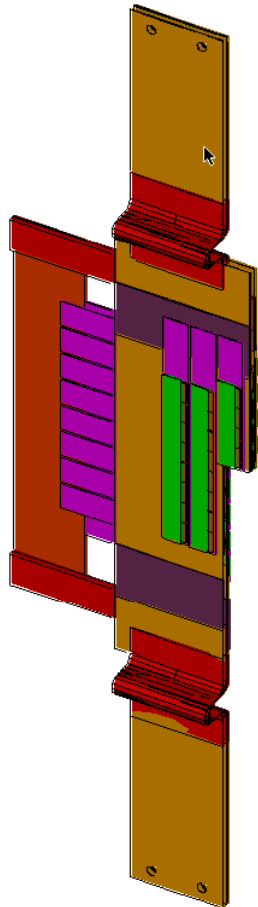
To VESPA



## REQUIREMENTS

- radiation tolerance corresponding to an integrated luminosity of  $\mathcal{O}(100\text{fb}^{-1})$   
( $\sim 10^{16} \text{ 1 MeV } n_{\text{eq}} / \text{cm}^2$ )
- Close coupling with trigger for optimal hadron trigger algorithm.
- Optimal spatial resolution
- Secure technology

## A very promising option for VESPA: hybrid pixel devices



- ▶ Measurement of 3D space points, with very few additional noise hits, implies excellent pattern recognition capabilities:

⇒ Fast vertex reconstruction

- Optimal radiation resistance (⇒ inner detector in ATLAS & CMS):
- Allows operation with smaller  $r_{\min}$  & higher luminosity without replacement for the duration of the experiment
- Low noise ( $\sim 200 e^-$  @ 25 ns) allows more precise charge interpolation & (in principle) thinner detectors.

## R&D activities - sensors

- Substrate material to ensure maximum radiation resistance (in collaboration with RD50):
  - p-type substrates
  - Magnetic Czochralski
- Alternative considered
  - 3D sensors

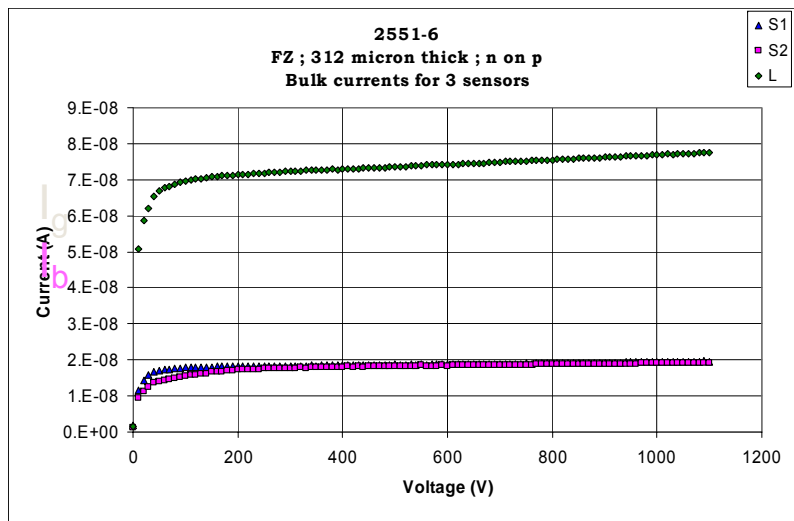
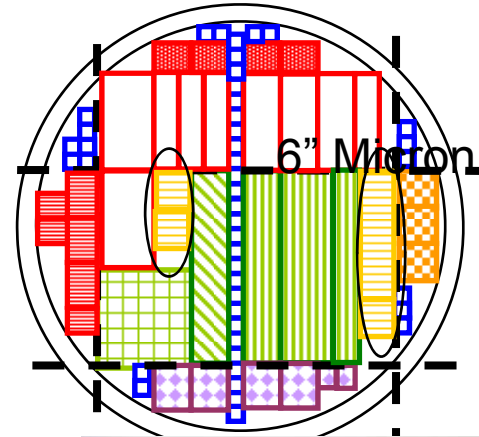
See also G. Casse & C. Parkes contributions

*University of Glasgow, University of Liverpool, Syracuse  
University working in the RD50 framework*



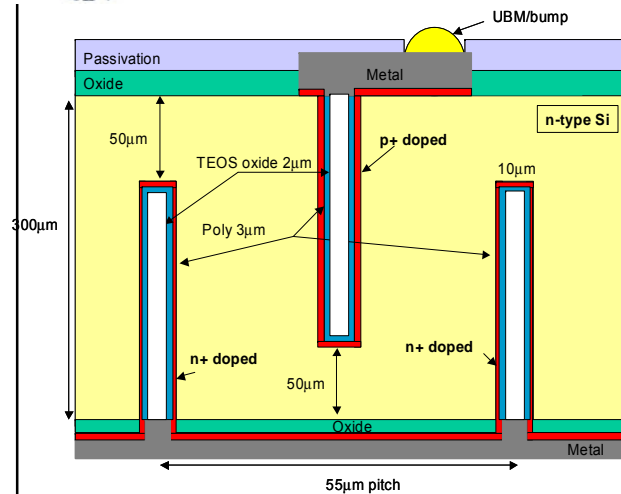
# n-on-p pixels

Syracuse/RD50 p-type  
“BTeV style” single chip  
pixel devices fabricated by  
Micron Semiconductor

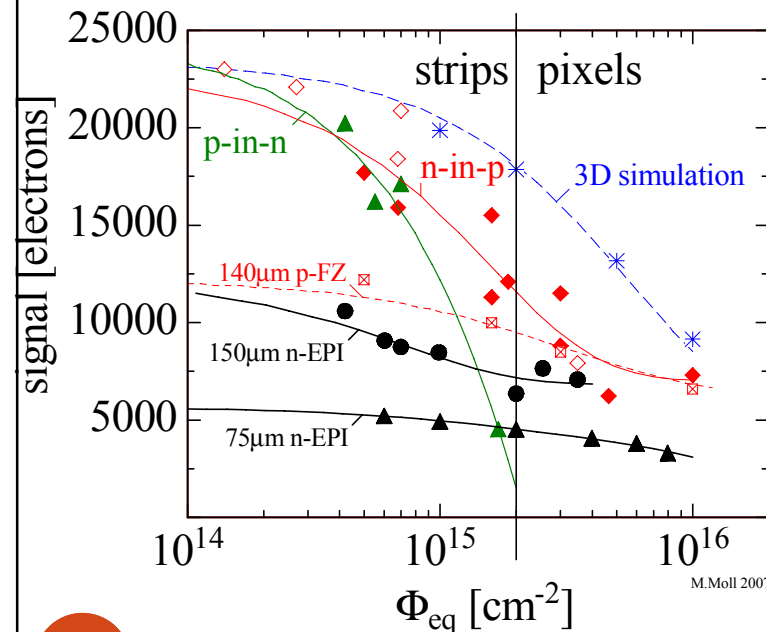


Depletion voltage 20-80 V unirradiated  
Started examining performance of irradiated  
detectors



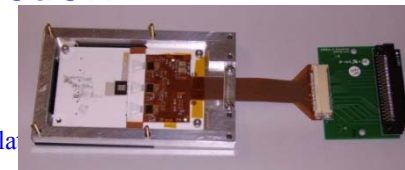


- 3D Detectors provide extreme rad hard solution
- novel double sided processing
- Glasgow/CNM produced strip and pixel detectors
- See talk from C.Parkes
- Pixel devices with ATLAS/BTeV pixel chip geometry in production

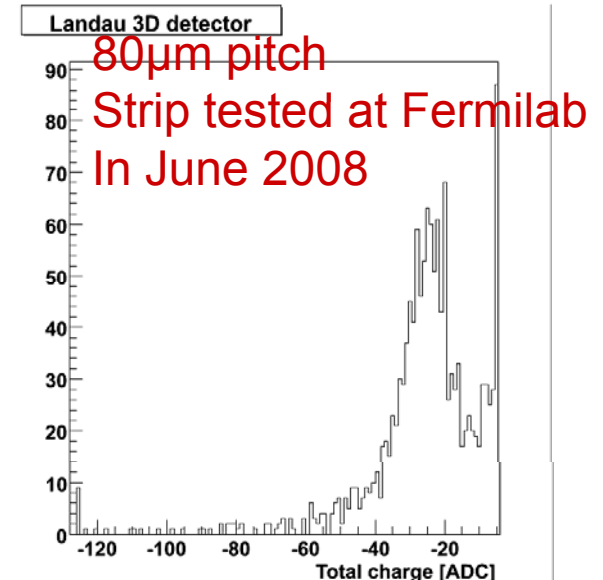


- \* Double-sided 3D, 250 µm, simula
- ♦ n-in-p (FZ), 280 µm [2,3]
- ◇ n-in-p (MCZ), 300µm [4,5]
- ▲ p-in-n (MCZ), 300µm [6]
- ⊠ n-in-p (FZ), 140 µm, 500V [7]
- p-in-n (EPI), 150 µm [8,9]
- ▲ p-in-n (EPI), 75µm [10]

[1] 3D, double sided, 250µm columns, 300µm substrate [Pennicard 2007]  
 [2] p-FZ, 280µm, (-30°C, 25ns), strip [Casse 2007]  
 [3] p-FZ, 280µm, (-30°C, 25ns), strip [Casse 2004]  
 [4] p-MCZ, 300µm, (-30°C, µs), pad [Bruzzi 2006]  
 [5] p-MCZ, 300µm, (-30°C, µs), strip [Bernadini 2007]  
 [6] n-MCZ, 300µm, (-30°C, 25ns), strip [Messineo 2007]  
 [7] p-FZ, 140µm, (-30°C, 25ns), strip [Casse 2007]  
 [8] n-EPI, 150µm, (-30°C, 25ns), strip [Messineo 2007]  
 [9] n-epi Si, 150µm, (-30°C, 25ns), pad [Kramberger 2006]  
 [10] n-epi Si, 75µm, (-30°C, 25ns), pad [Kramberger 2006]  
 See also: [M. Bruzzi et al. NIM A 579 (2007) 754-761]  
 [H.Sadrozinski, IEEE NSS 2007, RD50 talk]



Strip device  
readout with  
LHCb electronics  
software



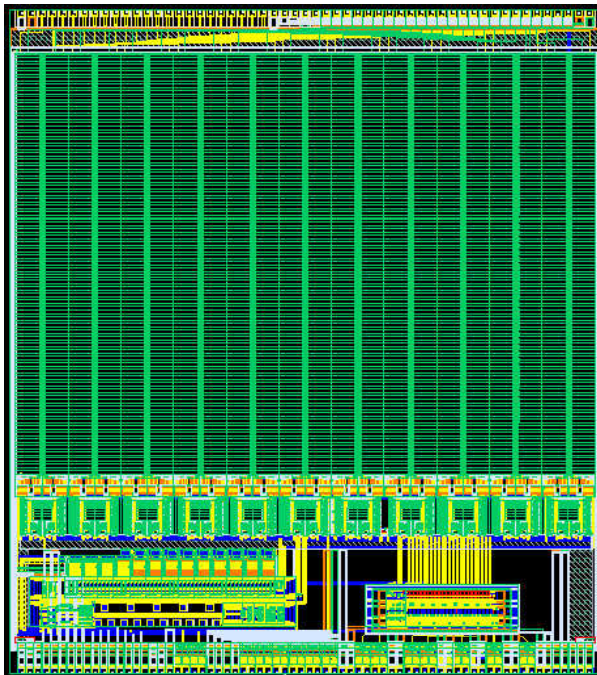


# Front-end electronics

- Must provide digitized data to trigger processor in real time:
  - On chip sparsification
  - On chip digitization
  - Push data to storage buffer within a beam crossing
- New smaller feature size technologies may allow smaller pixel size or higher spatial resolution

# An interesting prototype

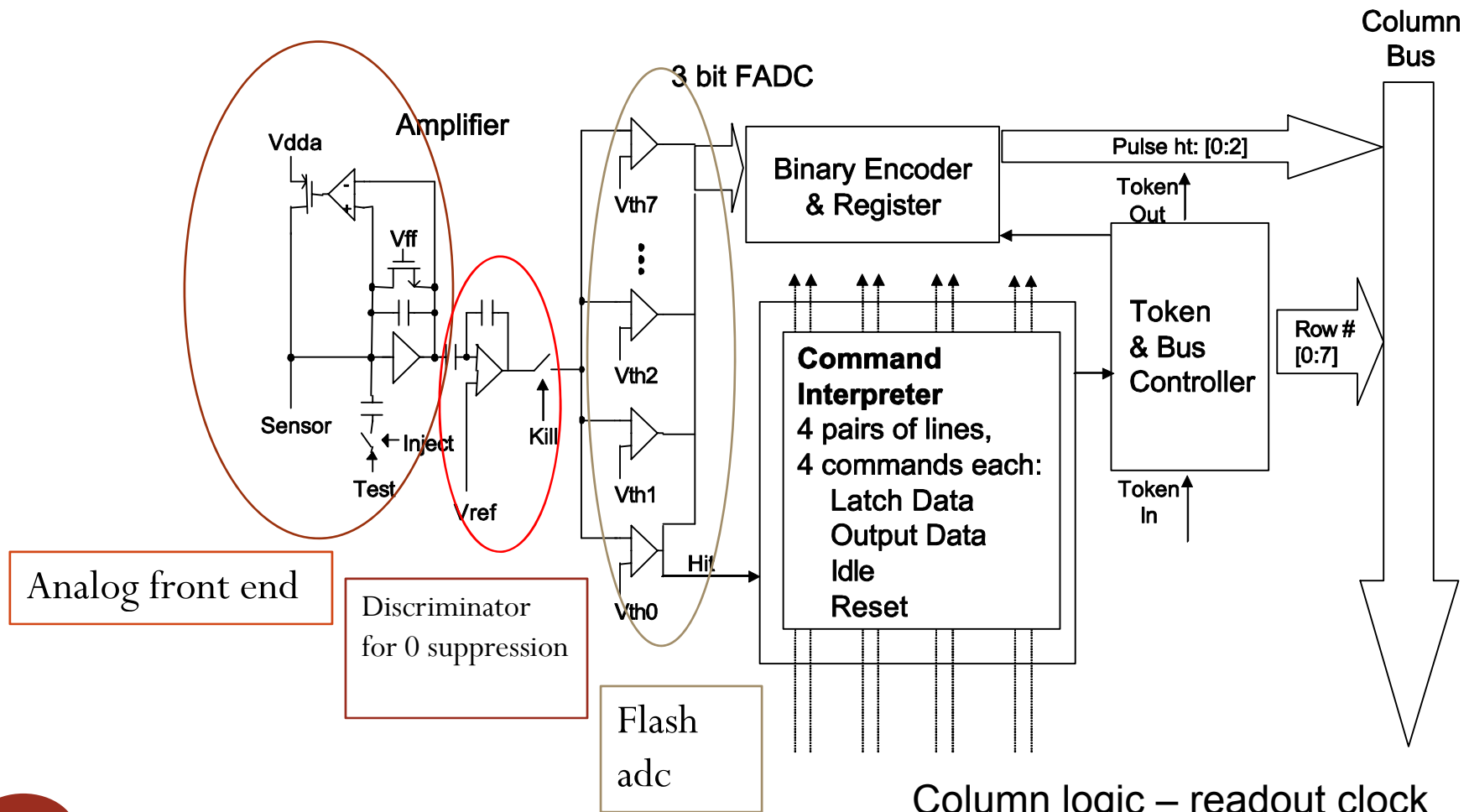
FPIX2



- ▶ 128X22 pixel electronics array with 1 flash ADC per cell providing sparsified hit information
- ▶ Tested with protons up to 87 Mrad with no degradation in analog performance and only minor changes required to bias conditions.
- ▶ Digital cells insensitive to total dose.
- ▶ No latch-up, no gate rupture.
- ▶ Single event upset cross sections measured, typically  $< 10^{-15} \text{ cm}^{-2}$  per bit.
- ▶ R&D Issues:
  - Data push speed
  - Timing parameters of the analog front-end
  - Match to optimized VESPA sensor
  - Migration to rad hard technology of the next decade

# Single cell readout & relevant times

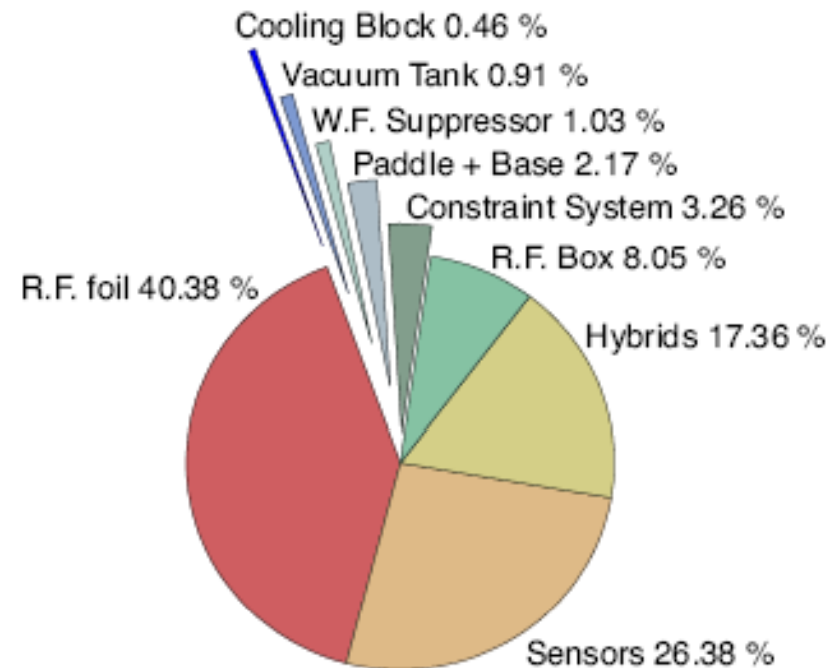
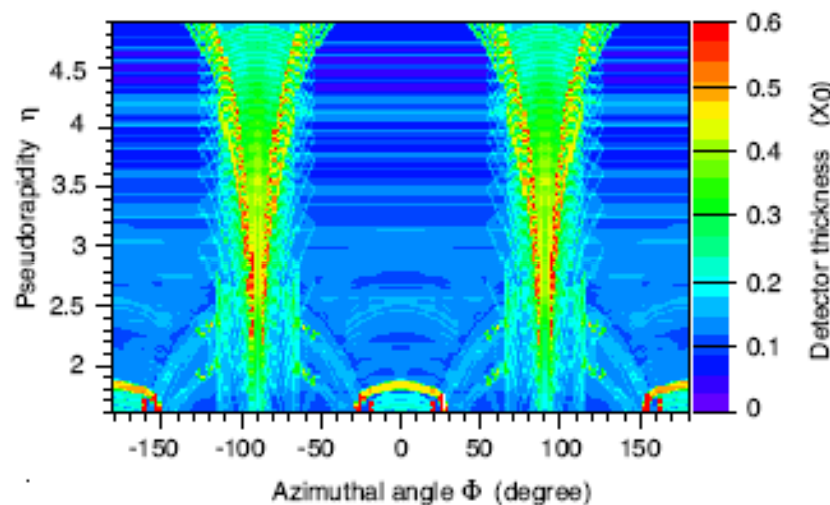
## Pixel Unit Cell



# Material budget optimization

- Relative contribution of the main components of the VELO to the average  $X_0$  of particles traversing the VELO in the range  $2.0 < \eta < 4.2$  is dominated by RF foil.
  - NIKHEF R&D on alternative RF design with less material

VELO now (see M. Tobin's talk)

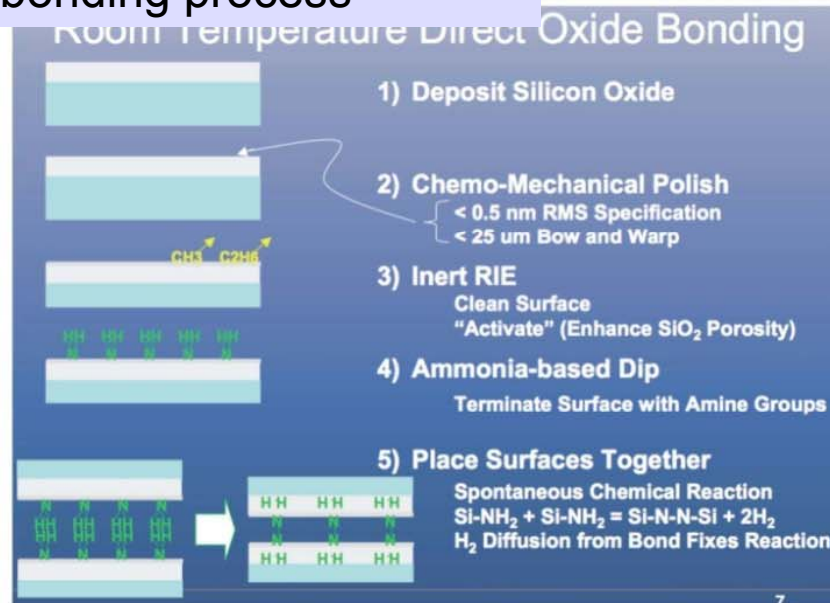


# Thin modules

• VELO Silicon budget is purely sensor, pixel solution includes front end electronics comparable with new approaches of 3D integration of thinner sensor/electronics assemblies

- In collaboration with Fermilab 2 approaches with Ziptronics & Tezzaron (more from G. Deptuch)
- European efforts with IZM
- Prototype devices with 100  $\mu\text{m}$  sensor/electronics

## Ziptronix direct oxide bonding process



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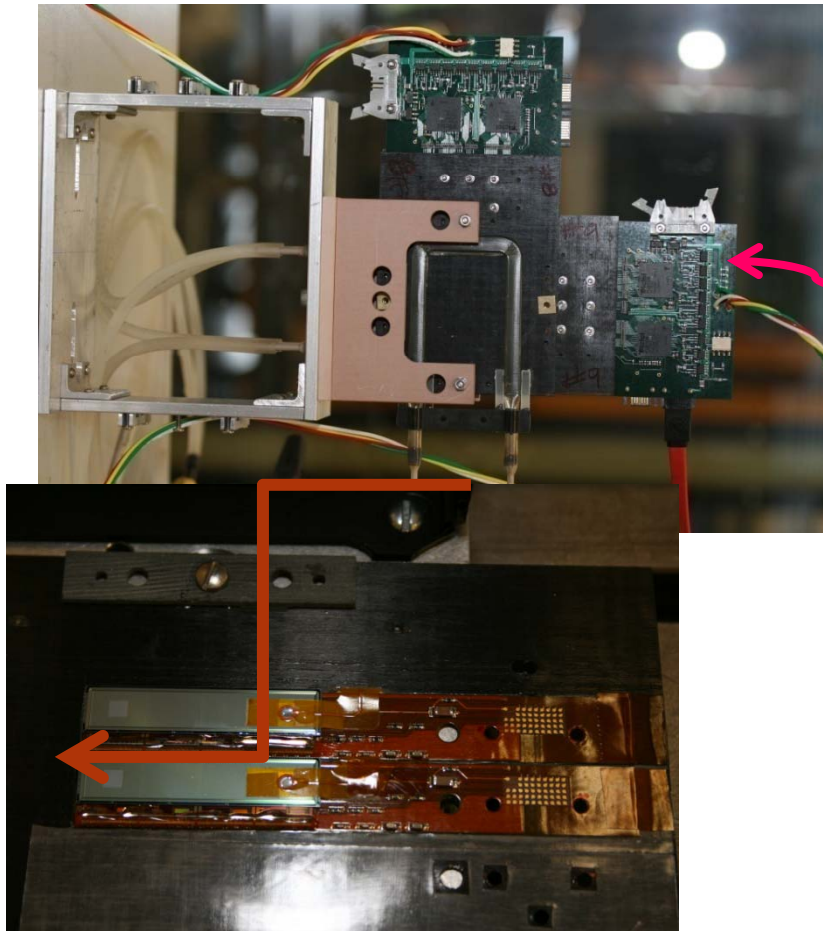


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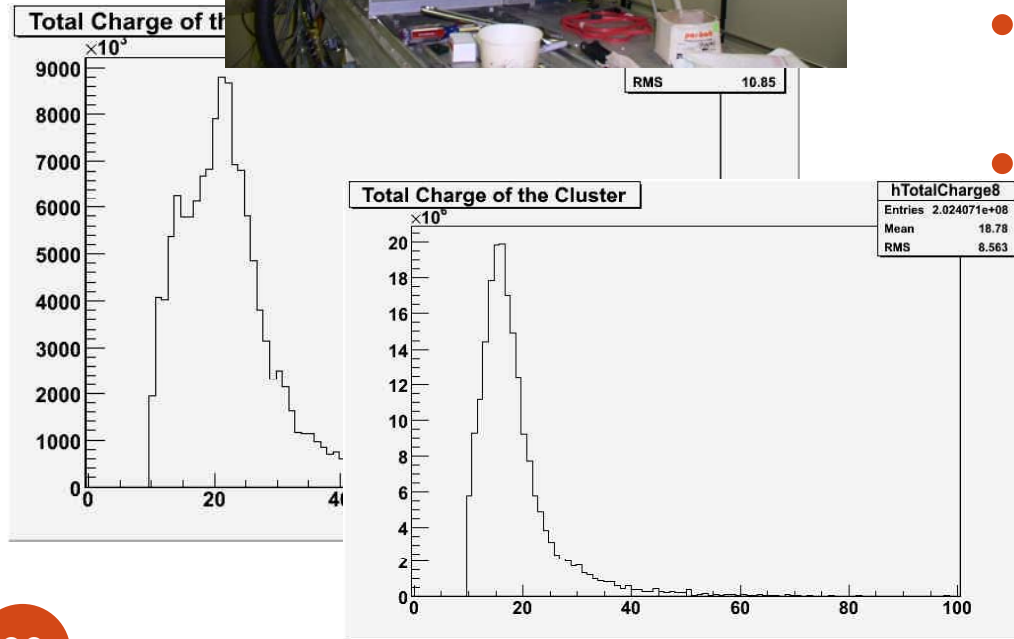
## Next steps

Large acceptance pixel telescope [3.5 cm x 3.5 cm aperture (270k pixels)]



- ▶ Detailed simulation to optimize system geometry
- ▶ Choice of sensor technology
- ▶ Study to determine the front end specifications (filtering properties, sparsification, flash ADC resolution, preferred technology)
- ▶ Intense test beam program utilizing pixel telescope facility at Fermilab Mtest (starting with T-971 which took the first data set in June 2008, only 3 pixel planes operational, follow up run with full pixel telescope planned for later this year)
- ▶ RF shield design
- ▶ TDR planned for 2010

# Sneak preview June FNAL test beam



- Tested 2 r sensitive VELO modules with non uniform level of irradiation, one fabricated with p-type technology & the other with n-type technology
  - Some data with 3 pixel planes
  - Soon: charge collection studies as a function of the radiation dose
- Next run with 4 fully functional pixel planes.



## Conclusions

- Quest for new physics discovery requires the ability to detect small deviations from the Standard Model predictions  $\Rightarrow$  VERY large samples of beauty and charm decays need to be collected.
- LHCb is poised to start soon the first phase of its program (integrated luminosity  $\sim 10 \text{ fb}^{-1}$ ) & is planning the next phase
- R&D items for the VERTEX detector:
  - Sensor optimization (segmentation & technology for optimum radiation hardness & fast and robust pattern recognition)
  - New front end electronics architecture and technology
  - New RF shield